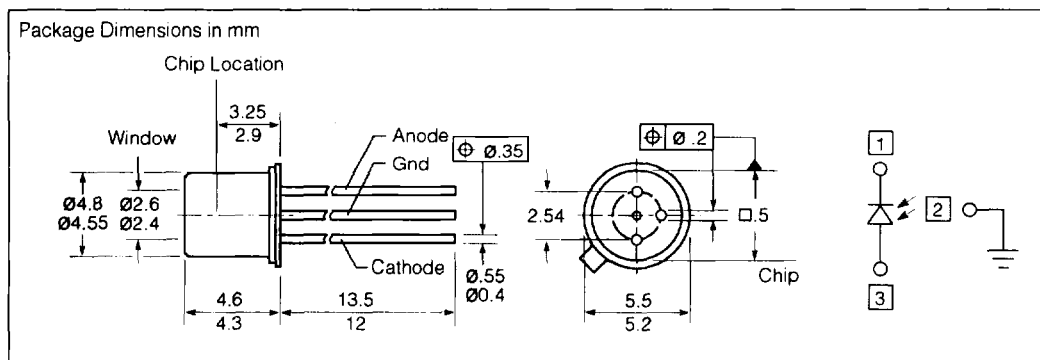




FEATURES

- InGaAs/InP PIN Photodiode
- Sensitive Receiver for the 2nd and 3rd Window (1300 nm and 1500 nm)
- Suitable for Bit Rates up to 1.2 Gbit/s
- Low Junction Capacitance
- Fast Switching Times
- Low Dark Current
- Low Noise
- High Reverse-Current Stability by Planar Structure
- Package: Hermetically Sealed 3-pin Metal Case, Similar to TO 18
- Application: Fiber Optic Communication Systems

Maximum Ratings

Operating and Storage Temperature Range (T_{OP} , T_{STG})	-40° to +85°C
Soldering Temperature (2 mm from case bottom), (T_S) $t_{MAX}=10$ s	260°C
Reverse Voltage (V_R)	20 V
Forward Current (I_F)	10 mA
Maximum Radiant Power into Optical Port	
$V_R > 5$ V (Φ_{PORT})	200 μ W
$V_R \leq 5$ V (Φ_{PORT})	1 mW

Characteristics ($T_A=25^\circ\text{C}$, all optical data refers to an optimally coupled 10/125 μm fiber.)

Parameter	Symbol	Value	Unit
Radiant Sensitive Area	$\varnothing$	75	μm
Spectral Sensitivity	S_λ	0.75 (≥ 0.7)	A/W
($\lambda=1300$ nm, $V_R=5$ V)			
Spectral Sensitivity Change within Operating Temperature Range ($\lambda=1300$ nm, $V_R=5$ V)			
	ΔS_λ	<0.2	%/K
Rise and Fall Time	t_R , t_F	0.3 (≤ 0.5)	ns
($R_L=50 \Omega$, $V_R=5$ V, $\lambda=1300$ nm, $\Phi_{PORT}=100 \mu\text{W}$)			
Total Capacitance	C_5	0.7 (≤ 1.2)	pF
($V_R=5$ V, $\Phi_{PORT}=0$, $f=1$ MHz)			
Dark Current ($V_R=5$ V, $\Phi_{PORT}=0$)	I_R	1 (≤ 10)	nA
Noise Equivalent Power ($V_R=5$ V)	NEP	3.3×10^{-14}	W/Hz
Optical Power Back Reflection into Optical Port	R	<1	%